

ABSTRACT

The present invention provides a composition enabling to form a fine negative photoresist pattern free from troubles such as surface roughness, bridge defects or unresolved defects, and the invention also provides a pattern formation method employing that composition. The composition is used for miniaturizing a resist pattern by applying to a negative resist pattern from a chemically amplified resist composition and fattening the resist pattern. This composition comprises a polymer comprising a repeating unit having an amino group or a polymer mixture, and a solvent, and further comprises a specific amount of an acid or indicates a specific pH value. The polymer mixture comprises polymers whose HSP distance, determined from Hansen solubility parameter, is 3 or more. In the pattern formation method, the composition is cast on a negative photoresist pattern beforehand obtained by development with an organic solvent developer and is then heated to form a fine pattern.